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Kind regards,

Team Nexperia



PMV160UP 20 V, 1.2 A P-channel Trench MOSFET Rev. 2 — 6 December 2011

Product data sheet

Product profile

1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a SOT23 (TO-236AB) small Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- 1.8 V R_{DSon} rated
- Very fast switching

Trench MOSFET technology

1.3 Applications

- Relay driver
- High-speed line driver

- High-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. **Quick reference data**

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V _{GS}	gate-source voltage			-8	-	8	V
I _D	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} 25 ^{\circ}\text{C}$	<u>[1]</u>	-	-	-1.2	Α
Static charact	teristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V}; I_D = -1.2 \text{ A}; T_j = 25 \text{ °C}$		-	170	210	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

Pinning information

Pinning information Table 2.

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	S	source	3	
3	D	drain	1	G S 017aaa257



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20 V, 1.2 A P-channel Trench MOSFET

Ordering information

Table 3. **Ordering information**

Type number	Package		
	Name	Description	Version
PMV160UP	TO-236AB	plastic surface-mounted package; 3 leads	SOT23

Marking

Table 4. **Marking codes**

Type number	Marking code ^[1]
PMV160UP	NH%

^{[1] % =} placeholder for manufacturing site code

20 V, 1.2 A P-channel Trench MOSFET

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V_{GS}	gate-source voltage			-8	8	V
I _D	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} 25 ^{\circ}\text{C}$	<u>[1]</u>	-	-1.2	Α
		$V_{GS} = -4.5 \text{ V}; T_{amb} = 100 ^{\circ}\text{C}$	<u>[1]</u>	-	-0.8	Α
I _{DM}	peak drain current	$T_{amb} = 25 ^{\circ}C$; single pulse; $t_p \le 10 \mu s$		-	-4	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	335	mW
			<u>[1]</u>	-	480	mW
		T _{sp} = 25 °C		-	2170	mW
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-dra	in diode					
Is	source current	T _{amb} = 25 °C	<u>[1]</u>	-	-0.5	Α

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

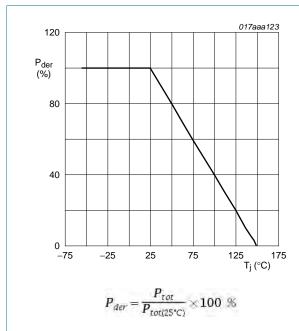
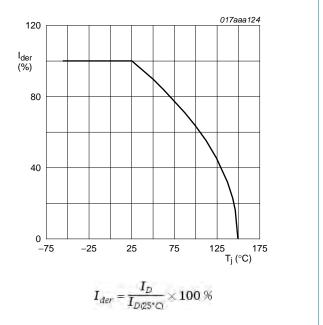
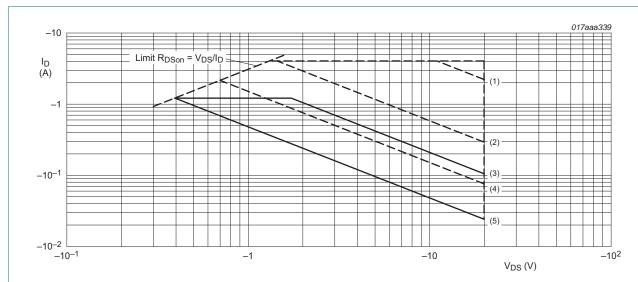


Fig 1. Normalized total power dissipation as a function of junction temperature



ig 2. Normalized continuous drain current as a function of junction temperature

20 V, 1.2 A P-channel Trench MOSFET



I_{DM} = single pulse

- (1) $t_p = 1 \text{ ms}$
- (2) $t_p = 10 \text{ ms}$
- (3) DC; $T_{sp} = 25 \, ^{\circ}\text{C}$
- (4) $t_p = 100 \text{ ms}$
- (5) DC; $T_{amb} = 25 \, ^{\circ}C$; drain mounting pad 6 cm²

Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

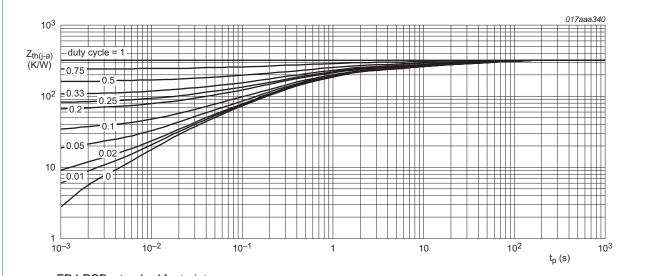
20 V, 1.2 A P-channel Trench MOSFET

6. Thermal characteristics

Table 6. Thermal characteristics

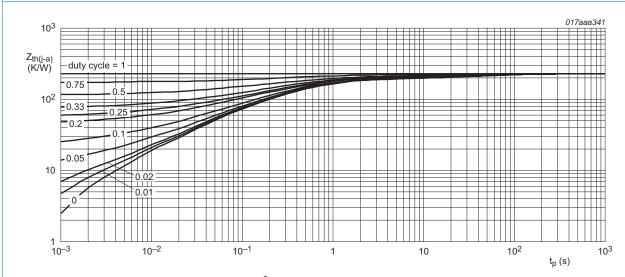
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air [1]	<u>[1]</u>	-	325	374	K/W
			<u>[2]</u>	-	227	260	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	50	60	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².



FR4 PCB, standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 6 cm²

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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7. Characteristics

Table 7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	-20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	-0.45	-0.7	-0.95	V
I _{DSS}	drain leakage current	$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μΑ
		$V_{DS} = -20 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	-10	μΑ
I _{GSS}	gate leakage current	$V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-100	nΑ
		$V_{GS} = 8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-100	nΑ
R _{DSon}	drain-source on-state	$V_{GS} = -4.5 \text{ V}; I_D = -1.2 \text{ A}; T_j = 25 \text{ °C}$	-	170	210	mΩ
	resistance	$V_{GS} = -4.5 \text{ V}; I_D = -1.2 \text{ A}; T_j = 150 \text{ °C}$	-	265	328	mΩ
		$V_{GS} = -2.5 \text{ V}; I_D = -1.1 \text{ A}; T_j = 25 \text{ °C}$	-	210	270	mΩ
		$V_{GS} = -1.8 \text{ V}; I_D = -0.5 \text{ A}; T_j = 25 \text{ °C}$	-	280	380	mΩ
g _{fs}	forward transconductance	$V_{DS} = -5 \text{ V}; I_D = -1.2 \text{ A}; T_j = 25 \text{ °C}$	-	3.7	-	S
Dynamic (characteristics					
Q _{G(tot)}	total gate charge	$V_{DS} = -10 \text{ V}; I_D = -1 \text{ A}; V_{GS} = -4.5 \text{ V};$	-	3.3	4	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	1	-	nC
Q_{GD}	gate-drain charge		-	0.5	-	nC
C _{iss}	input capacitance	$V_{DS} = -10 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	365	-	pF
Coss	output capacitance	T _j = 25 °C	-	42	-	pF
C _{rss}	reverse transfer capacitance		-	30	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; V_{GS} = -4.5 V; $R_{G(ext)}$ = 6 Ω ;	-	7	-	ns
t _r	rise time	$T_j = 25 ^{\circ}\text{C}; I_D = -1 ^{\circ}\text{A}$	-	26	-	ns
t _{d(off)}	turn-off delay time		-	35	-	ns
t _f	fall time		-	17	-	ns
Source-dr	rain diode					
V_{SD}	source-drain voltage	$I_S = -0.5 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_i = 25 \text{ °C}$	-	-0.7	-1.2	V

20 V, 1.2 A P-channel Trench MOSFET

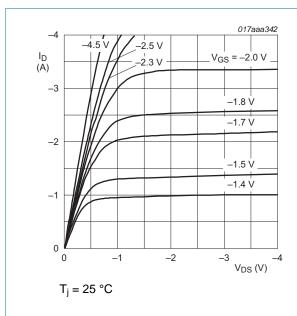
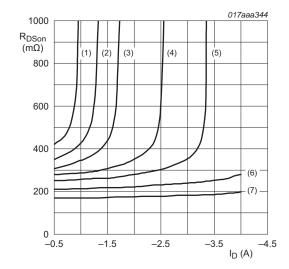


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values



T_i = 25 °C

(1) $V_{GS} = -1.4 \text{ V}$

(2) $V_{GS} = -1.5 \text{ V}$

(3) $V_{GS} = -1.6 \text{ V}$

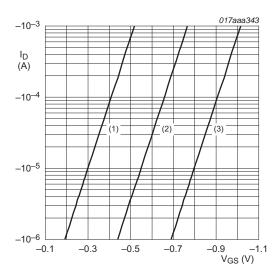
(4) $V_{GS} = -1.8 \text{ V}$

(5) $V_{GS} = -2.0 \text{ V}$

(6) $V_{GS} = -2.5 \text{ V}$

 $(7) V_{GS} = -4.5 V$

Fig 8. Drain-source on-state resistance as a function of drain current; typical values



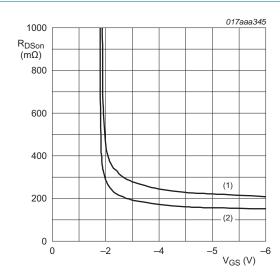
 $T_{j} = 25 \, ^{\circ}\text{C}; \, V_{DS} = -5 \, \text{V}$

(1) minimum values

(2) typical values

(3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage



 $I_D = -2.5 A$

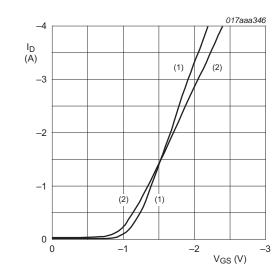
(1) $T_j = 150 \, ^{\circ}\text{C}$

(2) $T_j = 25 \,{}^{\circ}\text{C}$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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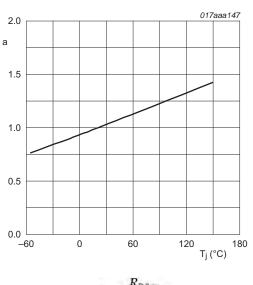


 $V_{DS} > I_D \times R_{DSon}$

(1)
$$T_j = 25 \, ^{\circ}C$$

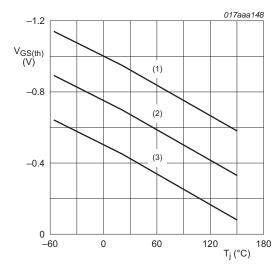
(2) $T_i = 150 \, ^{\circ}\text{C}$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$

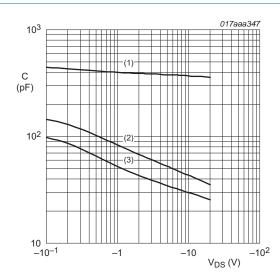
Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values



 $I_D = -0.25 \text{ mA}; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig 12. Gate-source threshold voltage as a function of junction temperature

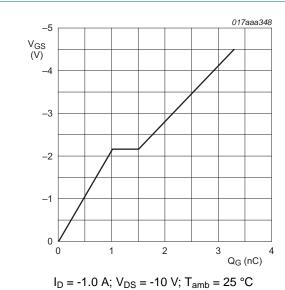


 $f = 1 MHz; V_{GS} = 0 V$

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

20 V, 1.2 A P-channel Trench MOSFET



V_{GS}(pl)

V_{GS}(pl)

V_{GS}(th)

V_{GS}

Q_{GS1}

Q_{GS2}

Q_{GS}

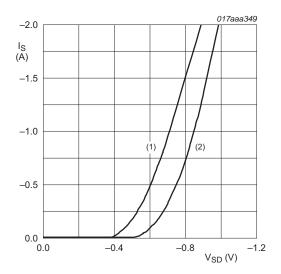
Q_G(tot)

017aaa137

Sate source voltage as a function of

Fig 14. Gate-source voltage as a function of gate charge; typical values

Fig 15. Gate charge waveform definitions



 $V_{GS} = 0 V$

(1) $T_j = 150 \, ^{\circ}\text{C}$

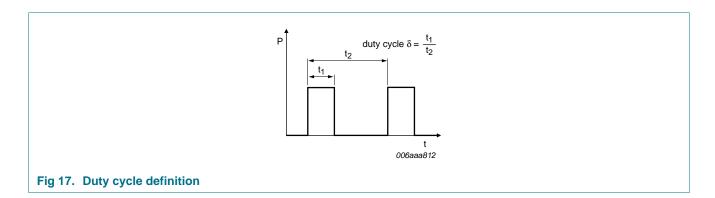
(2) $T_i = 25 \, ^{\circ}C$

Fig 16. Source current as a function of source-drain voltage; typical values

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20 V, 1.2 A P-channel Trench MOSFET

8. Test information



20 V, 1.2 A P-channel Trench MOSFET

9. Package outline

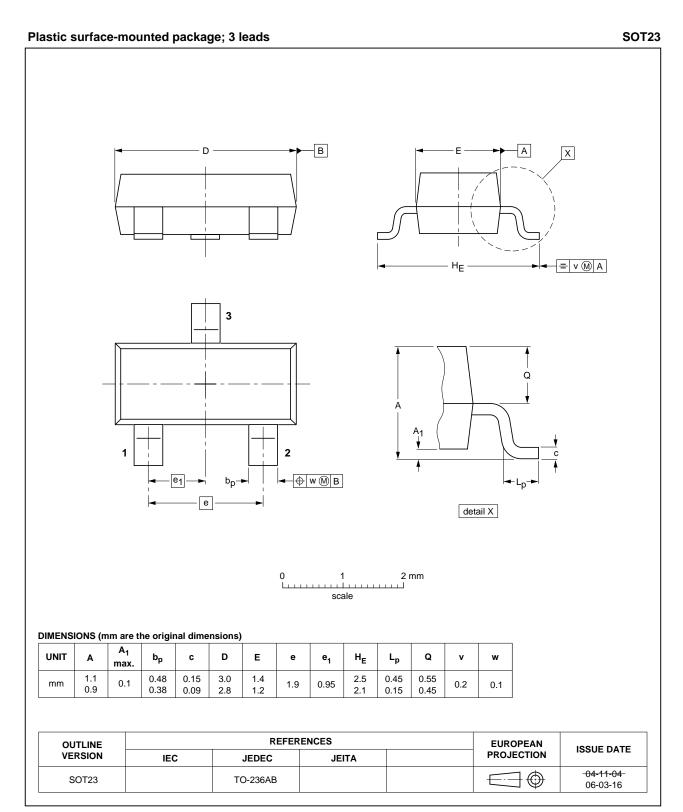


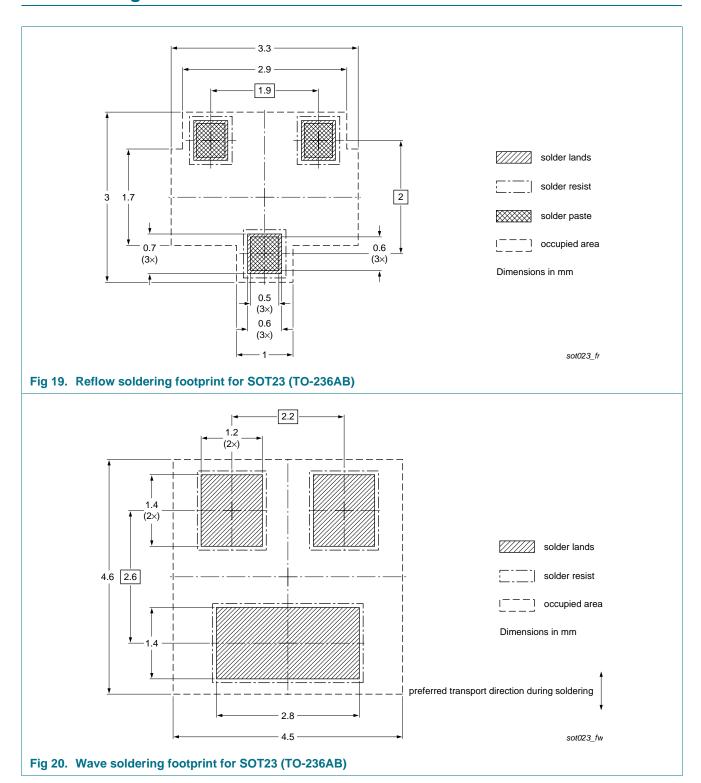
Fig 18. Package outline SOT23 (TO-236AB)

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10. Soldering



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11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PMV160UP v.2	20111206	Product data sheet	-	PMV160UP v.1
Modifications:	 7 "Characteristics" 	: V _{GSth} condition is correc	cted	
PMV160UP v.1	20110907	Product data sheet	-	-

20 V, 1.2 A P-channel Trench MOSFET

12. Legal information

12.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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